

6. (Once Amended) A semiconductor structure for storing charges, comprising:
an insulator layer; and
a uniform conductive layer having a compound formed from a first substance and a second substance, wherein the conductive layer includes a trace amount of the first substance, wherein the morphology of the semiconductor structure remains stable when the trace amount of the first substance is oxidized during crystallization of the insulator layer.
11. (Once Amended) A semiconductor structure for storing charges, comprising:
an insulator layer having a permittivity value greater than about 25; and
a uniform conductive layer having a compound, wherein the compound remains stable when the insulator layer is crystallized at a high temperature so as to decrease the charge leakage of the insulator layer.
16. (Once Amended) A semiconductor structure for storing charges, comprising:
an insulator layer having a permittivity value; and
a uniform conductive layer abuttingly coupled to the insulator layer and adapted to mitigate diffusion, wherein the crystalline structure of the insulator layer describes a desired lattice plane such that the permittivity value of the insulator layer is greater than about 25.
21. (Once Amended) A capacitor comprising:
a first electrode;
a dielectric that includes ditantalum pentoxide; and
a second uniform electrode having a compound that includes a first substance and a second substance, wherein the compound in an as-deposited state includes a substantial amount of the second substance so as to inhibit undesired diffusion at a high temperature, wherein the compound includes RuO_x , wherein the x is indicative of a desired number of atoms.

22. (Once Amended) A capacitor comprising:
- a first electrode;
 - a dielectric that includes ditantalum pentaoxide; and
 - a second uniform electrode having a compound that includes a first substance and a second substance, wherein the second electrode includes a trace amount of the first substance, wherein the morphology of the semiconductor structure remains stable when the trace amount of the first substance is oxidized during crystallization of the dielectric, wherein the compound includes RuO_x , wherein the x is indicative of a desired number of atoms.
23. (Once Amended) A capacitor comprising:
- a first electrode;
 - a dielectric that includes ditantalum pentaoxide; and
 - a second uniform electrode having a compound, wherein the crystalline structure of the dielectric describes a (001) lattice plane, wherein the compound includes RuO_x , wherein the x is indicative of a desired number of atoms.
24. (Once Amended) A capacitor comprising:
- a first electrode;
 - a dielectric having a first compound that includes a first substance and a second substance, wherein the first compound includes ditantalum pentaoxide; and
 - a second uniform electrode having a second compound that includes a third substance and a fourth substance, wherein the second electrode includes a trace amount of the third substance, wherein the second compound in an as-deposited state includes a substantial amount of the fourth substance, wherein the trace amount of the third substance is oxidized during the crystallization of the dielectric such that a diffusion of at least one of the first substance and the second substance is inhibited, wherein the crystalline structure of the dielectric describes substantially a (001) lattice plane, and wherein the second compound includes RuO_x , wherein the x is indicative of a desired number of atoms.

25. (Once Amended) A capacitor comprising:

a first electrode having a substance that is selected from a group consisting of TiN, TiON, WN_x , TaN, Ta, Pt, Pt-Rh, Pt-RhO_x, Ru, RuO_x, Ir, IrO_x, Pt-Ru, Pt-RuO_x, Pt-Ir, Pt-IrO_x, SrRuO₃, Au, Pd, Al, Mo, Ag, and Poly-Si;

a dielectric having a first compound that includes a first substance and a second substance, wherein the first compound includes ditantalum pentaoxide; and

a second uniform electrode having a second compound that includes a third substance and a fourth substance, wherein the second electrode includes a trace amount of the third substance, wherein the second compound in an as-deposited state includes a substantial amount of the fourth substance, wherein the trace amount of the third substance is oxidized during the crystallization of the dielectric such that a diffusion of at least one of the first substance and the second substance is inhibited, wherein the crystalline structure of the dielectric describes substantially a (001) lattice plane, and wherein the second compound includes RuO_x, wherein the x is indicative of a desired number of atoms.

51. (Once Amended) A memory device comprising:

an array of memory cells, wherein the array includes at least one capacitor that includes:

an insulator layer having a first compound that includes substances;

a uniform conductive layer having a second compound that includes a first substance and a second substance, wherein the second compound in an as-deposited state includes a substantial amount of the second substance so as to inhibit undesired diffusion of at least one substance of the first compound from the insulator layer;

an address decoder;

a row access circuitry;

a column access circuitry;

a controller; and

an input/output circuit.

52. (Once Amended) An electronic system comprising:
a plurality of circuit modules includes a plurality of dies, wherein at least one die includes at least one array of memory cells, wherein the array comprises at least one capacitor that includes:

an insulator layer having a first compound that includes substances;

a uniform conductive layer having a second compound that includes a first substance and a second substance, wherein the second compound in an as-deposited state includes a substantial amount of the second substance so as to inhibit undesired diffusion of at least one substance of the first compound from the insulator layer;

at least one transistor having a gate, drain, and source, wherein the drain is coupled to the second conductive layer;

a plurality of leads coupled to the plurality of dies to provide unilateral or bilateral communication and control; and

a user interface.

53. (Once Amended) A computer system comprising:

a processor;

a memory system that comprises a plurality of memory modules, wherein one of the plurality of memory modules comprises a plurality of memory devices, wherein at least one memory device comprises at least one array of memory cells, wherein the array comprises at least one capacitor that includes:

an insulator layer having a first compound that includes substances;

a uniform conductive layer having a second compound that includes a first substance and a second substance, wherein the second compound in an as-deposited state includes a substantial amount of the second substance so as to inhibit undesired diffusion of at least one substance of the first compound from the insulator layer; and

at least one transistor having a gate, drain, and source, wherein the drain is coupled to the second conductive layer;

a plurality of command links coupled to the plurality of memory devices to communicate at least one command signal;

a plurality of data links coupled to the plurality of memory devices to communicate data;

a memory controller;

at least one user interface device, wherein the at least one user interface device includes a monitor;

at least one output device, wherein the at least one output device includes a printer; and

at least one bulk storage device.